

FORM PTO-1449		Atty. Docket No. XA-9801A	Appln. No. 10/673,374
LIST OF DOCUMENTS CITED BY APPLICANT		Applicant Atsushi KUROKAWA et al.	

		Filing Date HEREWITH 9-30-03	Group 2813
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U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
CC	AA	5,077,231	12/31/91	Plumton et al.	438	170	
CC	AB	5,166,083	11/24/92	Bayraktaroglu	438	170	
CC	AC	5,268,315	12/07/93	Prasad et al.	438	314	
CC	AD	5,324,671	06/28/94	Bayraktaroglu	438	317	
CC	AE	5,672,522	09/30/97	Streit et al.	438	312	
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
CC	AJ	2001-210723	08/03/01	Japan			Abstract
	AK						
	AL						
	AM						
	AN						
	AO						

OTHER (including author, title, date, pertinent pages, etc.)

CC	AP	Chen et al., "High-Speed InGaP/GaAs HBT's Using a Simple Collector Undercut Technique to Reduce Base-Collector Capacitance," <u>IEEE Electron Device Letters</u> , Vol. 18, No. 7, July 1997, pp. 355-357.
CC	AQ	Ahmari et al., "InGaP/CaAs Heterojunction Bipolar Transistor Grown on a Semi-Insulating InGaP Buffer Layer," <u>IEEE Electron Device Letters</u> , Vol. 18, No. 11, November 1997, pp. 559-561.
	AR	

Examiner	C. Chaudhari	Date Considered
		5-04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.